

1. (Currently amended) A method for clearing slurry from a polishing pad in a CMP process, comprising:
 - placing a wafer substrate in contact with a polishing pad;
 - rotating said polishing pad;
 - providing a slurry dispense bar including a high pressure spray portion and a slurry dispense portion located over the polishing pad;
 - dispensing slurry from said slurry dispense bar on said polishing pad while said pad is rotating with said wafer substrate in contact with said pad;
 - terminating slurry dispense; and
 - while said wafer substrate is on the pad, spraying a high pressure fluid to remove slurry from between said wafer substrates and said pad with said high pressure spray portion of said slurry dispense bar.
2. (Original) The method of claim 1, wherein said high pressure spray includes water and is between 10 and 20 PSI.
3. (Original) The method of claim 2, wherein said high pressure spray is about 14 PSI.
4. (Original) The method of claim 1, including:
 - rotating said pad at a high speed during said spraying step.
5. (Original) The method of claim 4, wherein said high speed is between 90 and 120 RPMs.

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6. (Original) The method of claim 1, wherein said slurry dispense bar includes a splash guard located above said high pressure spray portion.
7. (Original) The method of claim 6, wherein said slurry dispense portion is located above said splash guard.
8. (Original) The method of claim 7, including a second slurry dispense portion located above said splash guard.
9. (Currently amended) A method for clearing slurry from a polishing pad in a CMP process, comprising:
- placing a wafer substrate in contact with a polishing pad;
 - rotating said polishing pad at a first speed;
 - dispensing slurry onto said polishing pad while said pad is rotating with said wafer substrates in contact with said pad;
 - terminating slurry dispense;
 - while said wafer substrate is on the pad, spraying a high pressure fluid around said wafer substrate to remove slurry from between said wafer substrate and said pad using said high pressure spray portion of said slurry dispense bar; and
 - rotating said pad at a second speed during said spraying step.

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10. (Original) The method of claim 9, wherein said high pressure spray is between 10 and 20 PSI.

11. (Original) The method of claim 10, wherein said second speed is between 60 and 200 RPMs.

12. (Original) The method of claim 10, wherein said second speed is between 90 and 120 RPMs.

Claims 13-20. (Cancelled).

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pressure fluid to remove slurry from between said wafer substrate and said pad with said high pressure spray portion of said slurry dispense bar (emphasis added). In other words, the wafer substrate is engaged in such a manner that slurry is removed from between it and the pad. Specifically, such passages fail to indicate where Huey's substrate 5 might be located during any of the described cleaning operations. Moreover, even assuming *arguendo* its presence is established in Huey, it still does not disclose an arrangement as defined by claim 1. It should further be noted that claim 1 has been amended to improve antecedent basis compliance by changing the unintended plural "substrates" in line 10 to --substrate-- as reflected in the claim listing.

Indeed, the Huey reference goes even further by suggesting the absence of the wafer during cleaning. For example, after polishing has been completed, arm assembly 60 is lifted and the remaining slurry is centrifugally expelled (step 106) before lowering the arm back into contact with the polish pad (step 108). (Huey, col. 5, lines 36-40). Such an operation would not likely provide desired results if the wafer substrate 5 is still present. Moreover, Huey emphasizes that it is "important for such fluids [cleaning fluids] and materials to be removed from the pad to ensure that the pad is free of contaminants prior to polishing a substrate." (Huey, col. 5, lines 55-61). Surely, Huey would not position substrate 5 in such a manner that it would impede this operation. Accordingly, there are several grounds to conclude that the Huey reference fails to expressly or inherently teach claim 1. It is therefore respectfully submitted that the rejection be withdrawn.

Besides the patentability of claim 1, further reasons support the patentability of rejected dependent claims. For example, claim 4 recites rotating the pad at a high speed during the

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